



#### 40V 175°C DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

#### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>C</sub> = +25°C
40V	$15m\Omega @ V_{GS} = 10V$	43.6A
	$25m\Omega @ V_{GS} = 4.5V$	33A

### **Description and Applications**

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Backlighting
- Power Management Functions
- DC-DC Converters

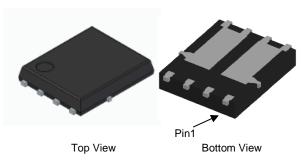
### **Features and Benefits**

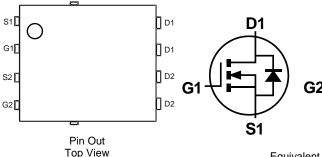
- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low R<sub>DS(ON)</sub> Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMTH4014LPDQ is suitable for automotive applications requiring specific change control and is AEC-Q101 qualified, is PPAP capable, and is manufactured in IATF16949:2016 certified facilities.

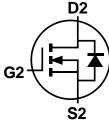
#### **Mechanical Data**

- Case: PowerDI<sup>®</sup>5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)

#### PowerDI5060-8 (Type C)







Equivalent Circuit

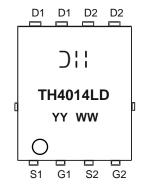
# **Ordering Information** (Note 4)

Part Number	Case	Packaging
DMTH4014LPDQ-13	PowerDI5060-8 (Type C)	2,500/Tape & Reel

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  - 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  - 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  - 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

# Marking Information

Notes:



);; = Manufacturer's Marking TH4014LD = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 19 = 2019) WW = Week (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated.



# **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V <sub>DSS</sub>	40	V	
Gate-Source Voltage	$V_{GSS}$	±20	V	
Continuous Drain Current (Note 6)	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	I <sub>D</sub>	43.6 30.8	А
Continuous Drain Current (Note 5)	$T_A = +25$ °C $T_A = +85$ °C $T_A = +100$ °C	I <sub>D</sub>	10.6 7.8 7.5	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%) (Note 6)	I <sub>DM</sub>	174	Α	
Maximum Continuous Body Diode Forward Current (Note 6)	Is	36	Α	
Avalanche Current, L = 0.3mH	I <sub>AS</sub>	11.7	Α	
Avalanche Energy, L = 0.3mH	Eas	20.5	mJ	

# **Thermal Characteristics**

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5) $T_A = +25^{\circ}C$		$P_{D}$	2.41	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	62.6	°C/W	
Thermal Resistance, Junction to Ambient (Note 5) T <sub>A</sub> = +85°C		$R_{\theta JA}$	65	°C/W
Total Power Dissipation (Note 6)	T <sub>C</sub> = +25°C	$P_{D}$	42.8	W
Thermal Resistance, Junction to Case (Note 6)		R <sub>0</sub> JC	3.5	°C/W
Operating and Storage Temperature Range		$T_{J_1}T_{STG}$	-55 to +175	°C

# $\textbf{Electrical Characteristics} \ (@T_A = +25^{\circ}C, \ unless \ \ \underline{otherwise \ specified.})$

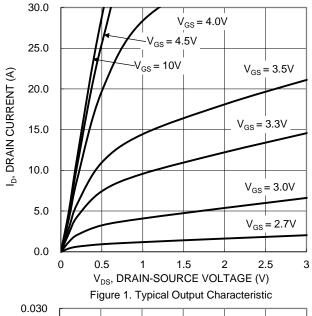
Characteristic		Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	40	_	_	V	$V_{GS} = 0V$ , $I_D = 1mA$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 32V, V_{GS} = 0V$	
Gate-Source Leakage		_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)	ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1	1.3	3	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
Static Drain-Source On-Resistance		_	11.8	15	mΩ	$V_{GS} = 10V, I_D = 20A$	
Static Dialif-Source Off-Resistance	R <sub>DS(ON)</sub>	_	17.9	25	11152	$V_{GS} = 4.5V, I_D = 15A$	
Diode Forward Voltage	$V_{SD}$	_	0.9	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C <sub>iss</sub>	_	733	_	pF		
Output Capacitance	Coss	_	235	_	pF	$V_{DS} = 20V, V_{GS} = 0V,$ f = 1MHz	
Reverse Transfer Capacitance	Crss	_	24	_	pF	1 = 11011 12	
Gate Resistance	Rg	_	1.3	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	_	5.2	_	nC		
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	_	10.2	_	nC		
Gate-Source Charge	Qgs	_	1.5	_	nC	$V_{DS} = 20V, I_{D} = 20A$	
Gate-Drain Charge	$Q_{gd}$	_	3.1	_	nC	1	
Turn-On Delay Time	t <sub>D(ON)</sub>	_	3.5	_	ns		
Turn-On Rise Time	t <sub>R</sub>	_	5.7	_	ns	$V_{DD} = 20V, V_{GS} = 10V,$ $R_{G} = 1.6\Omega, I_{D} = 20A$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	8.7	_	ns		
Turn-Off Fall Time	t <sub>F</sub>	_	1.8	_	ns		
Body Diode Reverse Recovery Time	t <sub>RR</sub>	_	11.9	_	ns	1 45A 31/44 400A/55	
Body Diode Reverse Recovery Charge	$Q_{RR}$	_	9.28	_	nC	$I_F = 15A$ , di/dt = 400A/ $\mu$ s	

5. Device mounted on FR-4 substrate PC board, 2oz. copper, with thermal bias to bottom layer 1inch square copper plate.

Notes:

<sup>6.</sup> Thermal resistance from junction to soldering point (on the exposed drain pad).7. Short duration pulse test used to minimize self-heating effect.





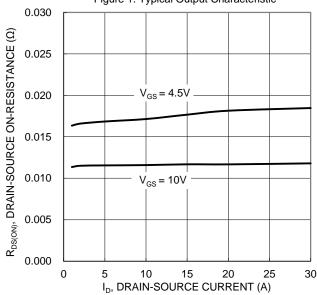


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

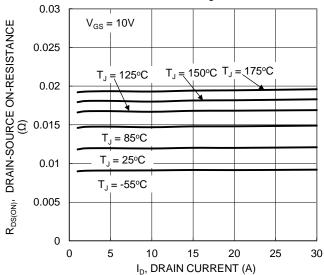


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

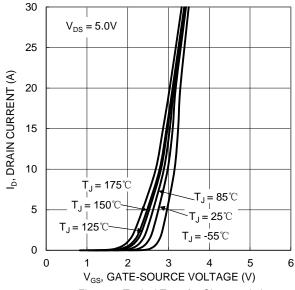


Figure 2. Typical Transfer Characteristic

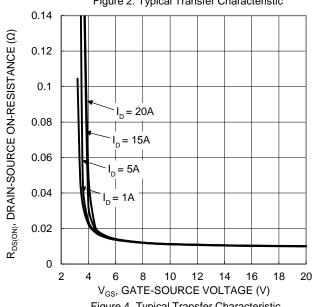


Figure 4. Typical Transfer Characteristic

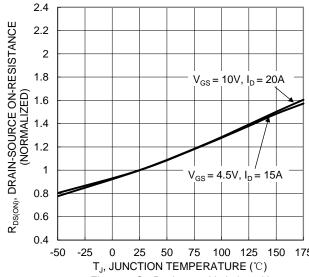


Figure 6. On-Resistance Variation with Temperature



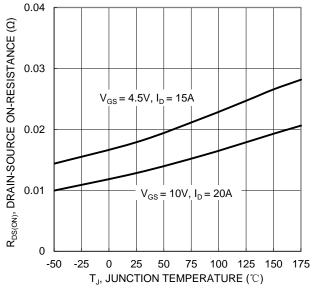


Figure 7. On-Resistance Variation with Temperature

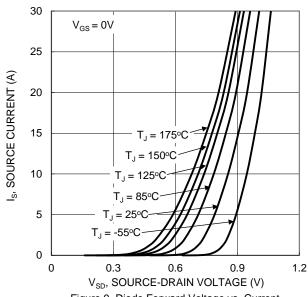


Figure 9. Diode Forward Voltage vs. Current

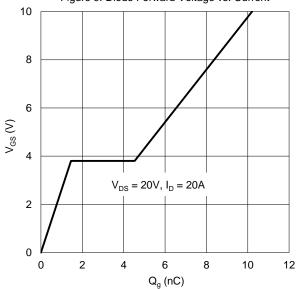


Figure 11. Gate Charge

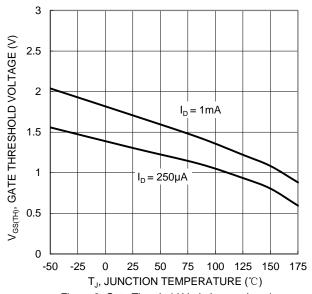


Figure 8. Gate Threshold Variation vs. Junction Temperature

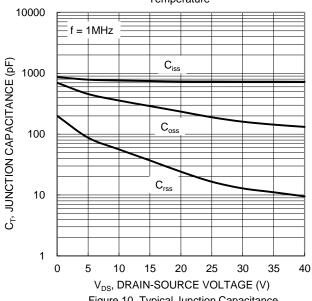


Figure 10. Typical Junction Capacitance

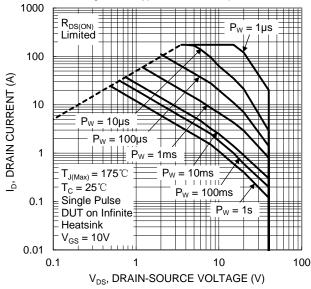


Figure 12. SOA, Safe Operation Area



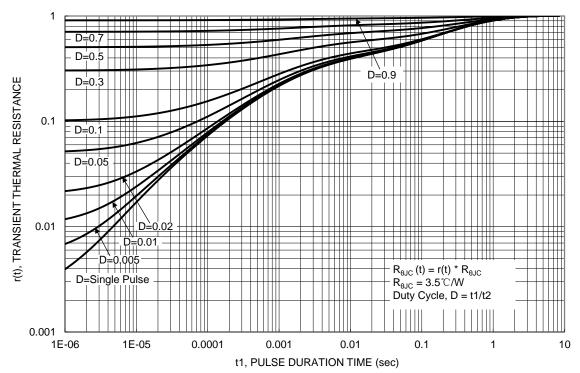


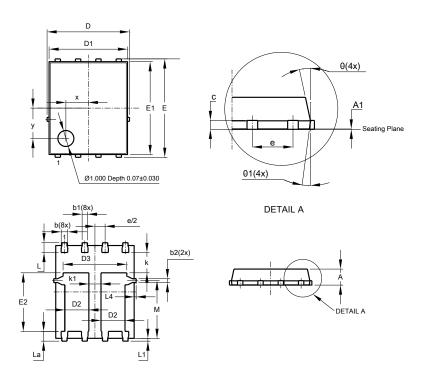
Figure 13. Transient Thermal Resistance



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8 (Type C)

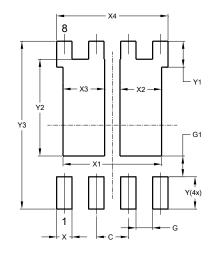


PowerDI5060-8 (Type C)					
Dim	Min	Тур			
Α	0.90	1.10	1.00		
<b>A</b> 1	0	0.05	0.02		
b	0.33	0.51	0.41		
b1	0.300	0.366	0.333		
b2	0.20	0.35	0.25		
С	0.23	0.33	0.277		
D	,	5.15 BSC	;		
D1	4.85	4.95	4.90		
D2	1.40	1.60	1.50		
D3	-	-	3.98		
Е	6.15 BSC				
E1	5.75	5.85	5.80		
E2	3.56	3.76	3.66		
е	1.27BSC				
k	-	-	1.27		
k1	0.56				
L	0.51	0.71	0.61		
La	0.51	0.71	0.61		
L1	0.05	5 0.20 0.1			
L4	-	-	0.125		
M	3.50	3.71	3.605		
X	-	-	1.400		
у	-	-	1.900		
θ	10°	12°	11°		
θ1	6° 8° 7°				
All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8 (Type C)



Dimensions	Value		
2	(in mm)		
С	1.270		
G	0.660		
G1	0.820		
Х	0.610		
X1	3.910		
X2	1.650		
Х3	1.650		
X4	4.420		
Y	1.270		
Y1	1.020		
Y2	3.810		
Y3	6.610		



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